

# 2SB903/2SD1212

# 30V/12A High-Speed Switching Applications

## **Applications**

· Suitable for relay drivers, high-speed inverters, converters, and other general large-current switching applications.

#### **Features**

- $\cdot$  Low collector-to-emitter saturation voltage :  $V_{CE(sat)}\!\!=\!\!(-)0.5V$  (PNP), 0.4V (NPN) max.
- · Large current capacity.

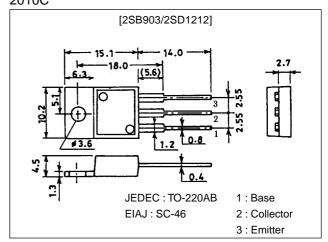
(): 2SB903

# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

# **Package Dimensions**

unit:mm 2010C



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)30	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(–)6	V
Collector Current	IC		(–)12	Α
Collector Current (Pulse)	I <sub>CP</sub>		(-)20	Α
Collector Dissipation	PC		1.75	W
		Tc=25°C	35	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(–)0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)0.1	mA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	70*		280*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)6A	30			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A		120		MHz

 $\mbox{\ensuremath{*}}$  : The 2SB903/2SD1212 are graded as follows by  $\mbox{\ensuremath{h_{FE}}}$  at 1A :

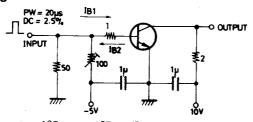
70 Q 140 100 R 200 140 S 280

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## 2SB903/2SD1212

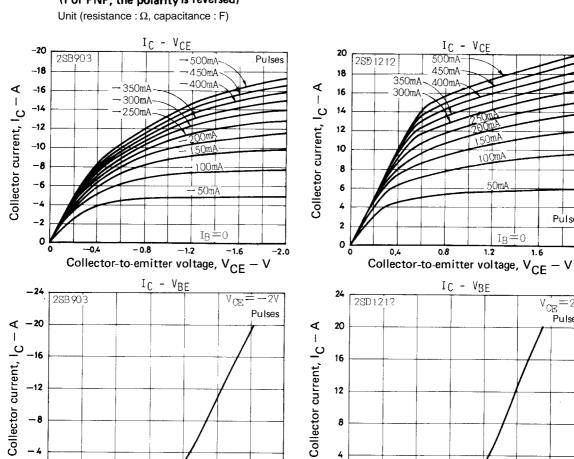
Parameter	Symbol	Conditions	Ratings			Unit
r aidilletei			min	typ	max	Offit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)5A, I <sub>B</sub> =(-)0.25A			(-0.5)	V
					0.4	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)1mA, I <sub>E</sub> =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(−)1mA, R <sub>BE</sub> =∞	(-)30			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)1mA, I <sub>C</sub> =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit		(0.1)		μs
				0.2		μs
Storage Time	t <sub>stg</sub>	See specified Test Circuit		(0.3)		μs
				0.5		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit		0.03		μs

### **Switching Time Test Circuit**



 $10I_{B1} = -10I_{B2} = I_C = 5A$ (For PNP, the polarity is reversed)

-0.2 -0.4 -0.6 -0.8 -1.0 -1.2 Base-to-emitter voltage, V<sub>BE</sub> - V

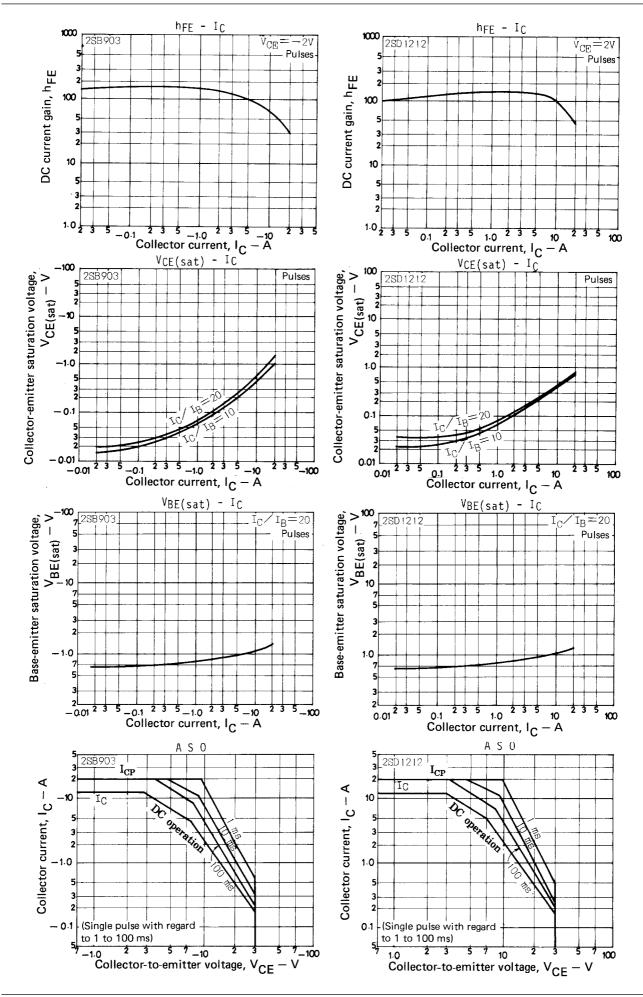


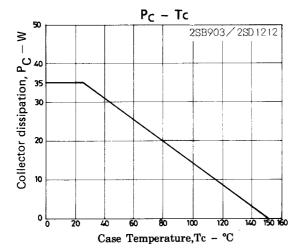
0,

0.2 0.4 0.6 0.8 1.0 1.2 Base-to-emitter voltage,  $V_{\mbox{\footnotesize BE}}-V$ 

Pulses

V<sub>CE</sub>=2V Pulses





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